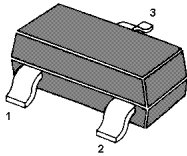
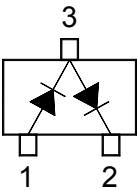


MMBD172SE

SILICON EPITAXIAL PLANAR DIODE

for VHF~UHF band RF attenuator applications



Marking Code: **FP**
TO-236 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^{\circ}\text{C}$)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	50	V
Forward Current	I_F	50	mA
Junction Temperature	T_J	125	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 125	$^{\circ}\text{C}$

Characteristics at $T_a = 25\text{ }^{\circ}\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
Forward Voltage at $I_F = 10\text{ mA}$	V_F	-	-	1	V
Reverse Voltage at $I_R = 10\text{ }\mu\text{A}$	V_R	50	-	-	V
Reverse Current at $V_R = 50\text{ V}$	I_R	-	-	0.1	μA
Total Capacitance at $V_R = 50\text{ V}$, $f = 1\text{ MHz}$	C_T	-	0.25	-	pF
Series Resistance ¹⁾ at $I_F = 10\text{ mA}$, $f = 100\text{ MHz}$	r_s	-	7	-	Ω

¹⁾ C_T is measured by 3 terminal method with capacitance bridge.

